

## PVD Products PLD-2000/3000



## PLD-3000 shown with optional 2 position loadlock and A COMPex 200 Series Excimer Laser

The PVD Products PLD-2000/3000 is capable of depositing high quality uniform films on substrates up to 2" or 3" (75-mm) in diameter, respectively. Our systems use a 304L SS box chamber with front-mounted hinged door providing quick access for easy substrate and target changes. The chamber has multiple user accessory ports for target and substrate viewing, a magnetron or ion source and spectroscopy. A blackbody style oven with a bank of IR heat lamps is used for substrate heating. Transparent substrates such as sapphire, LaAlO<sub>3</sub>, and MgO can be heated to 850°C without the use of a thermal bonding agent (such as silver paste) or clamping. Silicon or other absorbing substrates may be heated to 950°C. Temperature uniformity of  $\pm 3^{\circ}$  is readily

achievable over 3" diameter substrates. heater is surrounded by a water-cooled housing that keeps the chamber walls, targets, and gears cool during deposition. A complete enclosed optical train which rasters the laser beam over a large diameter rotating targets is included. The optical train also utilizes our Intelligent Window with in-the-chamber energy monitoring. Complete vacuum gauging along with a 500 L/sec molecular drag turbo pump is provided to achieve pressures below 5 X 10<sup>-7</sup> Torr. electropneumatic valves are controlled from a rack-mounted pump chassis. Constant pressure is obtained by using a MFC, capacitance manometer, butterfly valve, along with a closedloop pressure control unit. This system is ideal for materials and device related research or prototype production.





## PLD-2000/3000 System Specifications:

<u>Maximum substrate size</u>: **PLD 2000**: Can handle One (1) 2-inch wafer or multiple smaller samples per customer requirement. **PLD-3000**: Can handle One (1) 3-inch, or one 2-inch, or multiple small substrates per customer requirement.

Maximum substrate temperature: 950°C (in oxygen) for non-transparent substrates such as Silicon, and 850°C for transparent substrates (such as LaAlO<sub>3</sub>). *No thermal paste or bonding required.* 

Temperature uniformity: ± 3°C across 3-inch diameter Si substrate
Operating Pressure Range: 5 x 10<sup>-4</sup> Torr base to 300 mTorr
Target Size: The PLD-2000 includes four 3" diameter targets. The PLD-3000 includes three 4-inch diameter targets (easily adaptable to other sizes)
Film Thickness Uniformity: ± 5 % over 90% of a 3" diameter substrate for 500 nm thick film using 4" diameter target.

<u>Target to Substrate (Throw) Distance</u>: Variable from ~75 to 125 mm (may affect maximum temperature, temperature uniformity, and thickness)

Raster path length: ~3.8 inches

Nominal Angle of incidence of the laser beam on target: 60°

Base Pressure of the Main Chamber: P < 5 x 10<sup>-7</sup> Torr guaranteed, with system at room temperature without targets in the chamber.

Base Pressure with Load Lock: P<5 x 10<sup>-8</sup> Torr guaranteed, with system at room temperature without targets in the chamber. UHV Option Available Operational Wavelength: 248 nm (KrF) or 193 nm (ArF) .

## PLD 2000/3000 System Options:

Load locks for fast turnaround time and improved main chamber base pressure. UHV Bake Out for pressure below 7 x 10<sup>-9</sup> Torr Additional MFC's Custom Substrate Holders

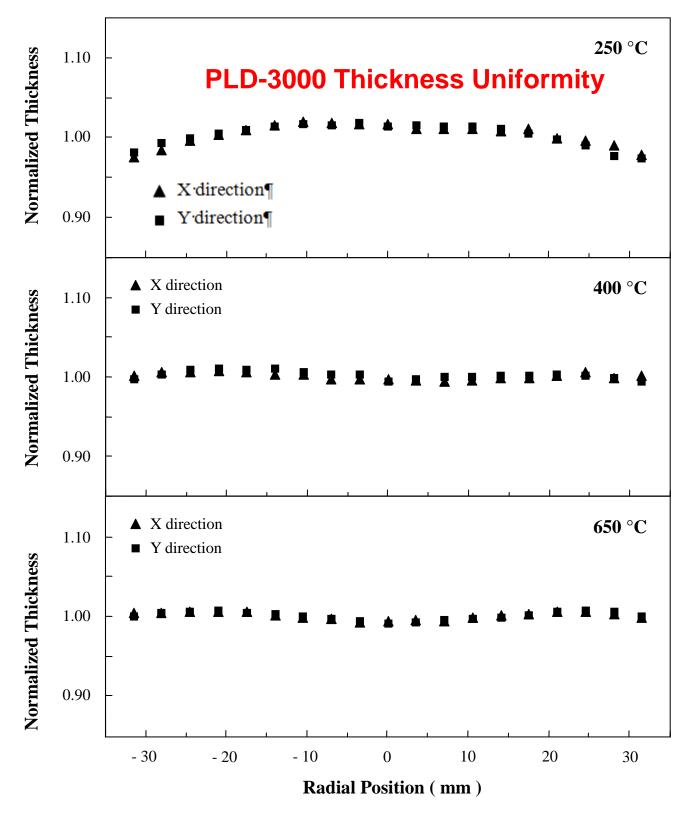
**Note:** Specifications subject to change.



PLD-2000 four position target carousel assembly





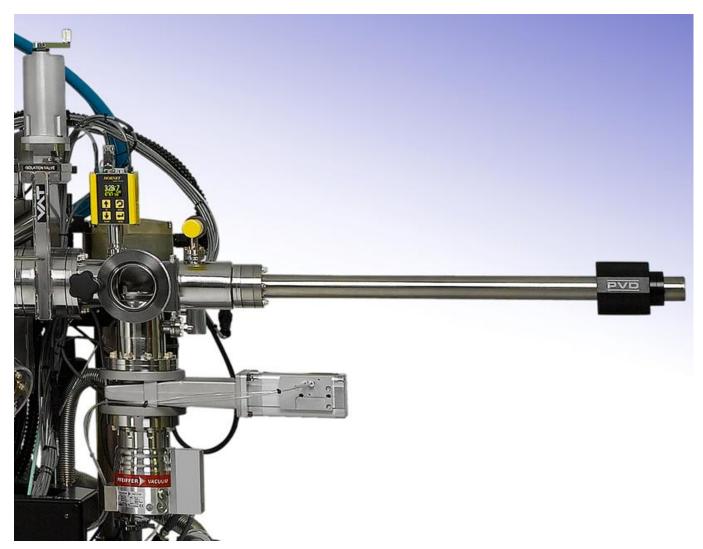


Normalized film thickness from three  $Ta_2O_5$  films deposited onto a 3-inch silicon substrates at a) 250°C, b) 400°C, and c) 650°C, respectively.

Reference: Boughaba et. al. Mater. Res. Soc Proc., Vol: 567, 527







PLD-2000 Dual Wafer Loadlock Assembly. This loadlock allows the removal and insertion of a sample into the chamber in one pump down cycle basically doubling the speed with which wafers can be transferred.



Examples of various types of substrate holders available with the PLD-2000/3000 system

